

Multi-Channel

Silicon ESD Protector Overvoltage Protection Device

PRODUCT: SESD0402Q2UG-0030-088

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Specification Status: RELEASED

BENEFITS

- Low capacitance; provides lowest insertion loss for high speed data signals
- Small footprint and low profile multi-channel ESD array helps to optimize board space
- Flow-through and single connection design helps routing PCB matched-impedance high speed data lines
- Helps protect electronic circuits against damage from Electrostatic Discharge (ESD), surge and cable discharge events
- Assists equipment to pass IEC61000-4-2, level 4 testing

FEATURES

- Low Capacitance: 0.30 pF (typ)
- Low leakage current : 25nA @ 5V (typ)
- Low clamping voltage : +13.0 (typ)
 @ (tp=8x20µs, lpp=2.5A)
- ESD maximum rating per IEC61000-4-2 standard:
 - ±22kV contact discharge
 - o ±22kV air discharge
- Surge: 2.5A (max) @ (tp=8x20µs) per IEC61000-4-5
- Small size and low profile: XDFN packages

APPLICATIONS

- Consumer, mobile and portable electronics
- Tablet PC and external storage with high speed interfaces
- Ultra-high speed data lines
- USB 3.0/2.0, HDMI 1.3/1.4, DisplayPort, V-by-One HS, and LVDS interfaces
- Applications requiring high ESD performance in small DFN packages

MATERIALS INFORMATION

RoHS Compliant E

ELV Compliant Halogen Free * Lead Free

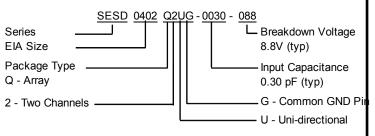


ΗF

* Halogen Free refers to: Br≤900ppm, Cl≤900ppm, Br+Cl≤1500ppm SESD devices meet MSL-1 Requirements DFN case epoxy meets UL 94 V-0



PART NUMBERING

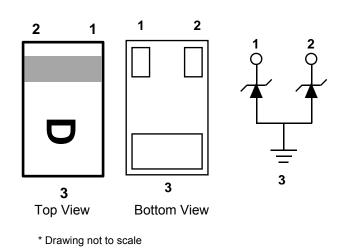


PART MARKING



Factory Code Marking - Factory: Single alphanumeric character

PIN CONFIGURATION AND SCHEMATIC





DEVICE MAXIMUM RATING

ESD Withstand ⁽¹⁾ (IEC 61000-4-2, level 4)		Temperature		Peak Current (tp=8x20µs)
Contact (kV)	Air (kV)	Operating (°C)	Storage (°C)	lpp (A)
± 22	± 22	-55 to +125	-55 to +150	2.5

(1) 22kV @ 10 pulses; 20kV @ 100 pulses; 8kV @ 1,000 pulses (under IEC6100-4-2)

• Device maximum rating @ T = 25°C, unless otherwise specified.

• Caution: Stress exceeding Device Maximum Ratings may damage the device.

Prolonged exposure to stresses above the recommended operating conditions may affect device reliability.

DEVICE ELECTRICAL CHARACTERISTICS

Input Capacitance @ V _R = 0V, f = 3GHz (pF)	Breakdown Voltage (V) V _{BR} @ I _T =1mA (V)	Reverse Working Voltage (V)	Reverse Leakage Current (A) I _L @ V _{RWM} =5.0V (nA)	Clamping Voltage V _{CL} @ lpp=2.5A (V)
Тур	Тур	Тур	Тур	Тур
0.30	+8.80 / -0.80	7.00	25.0	+13.0

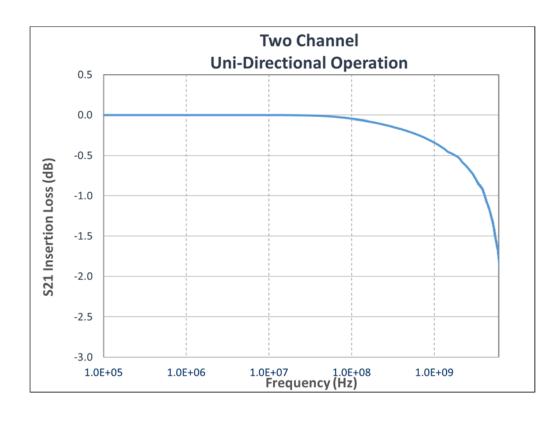
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• All device electrical characteristics @ T = 25°C, unless otherwise specified.

FIGURE 1. INSERTION LOSS DIAGRAM



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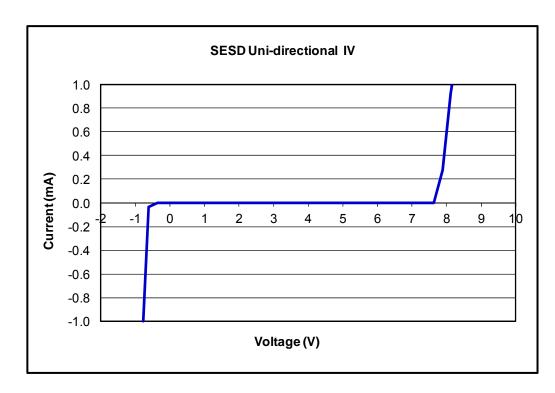


FIGURE 2. DEVICE IV CURVE

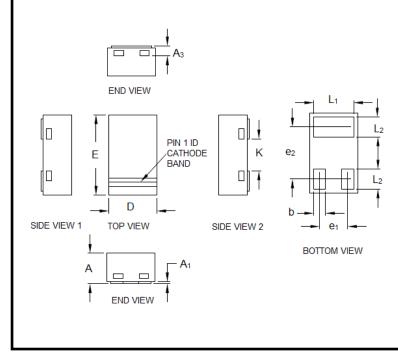
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DEVICE DIMENSIONS



	SESD0402Q2UG-0020-090					
	Millimeters (mm)			Inches (in)		
Dim	Min	Nom	Max	Min	Nom	Max
Α	0.33	0.38	0.43	0.013	0.015	0.017
A1	0		0.05	0		0.002
A3	0.13 ref.			0.005 ref.		
D	0.55	0.60	0.65	0.022	0.024	0.026
E	0.95	1.00	1.05	0.037	0.039	0.041
к	0.35	0.40	0.45	0.014	0.016	0.018
L1	0.45	0.50	0.55	0.018	0.020	0.022
L2	0.20	0.25	0.30	0.008	0.010	0.012
b	0.10	0.15	0.20	0.004	0.006	0.008
e1	0.35 BSC		0.014 BSC			
e2	0.65 BSC			0.026 BSC		

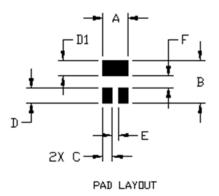
BSC - Basic Spacing between Centers



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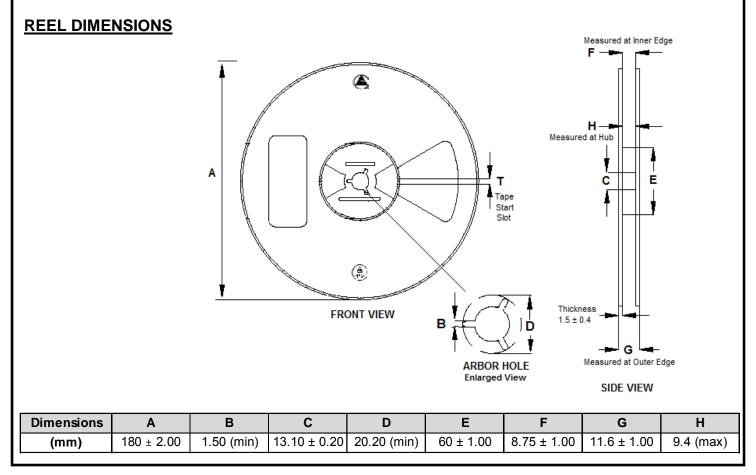
RECOMMENDED LANDING PATTERN:



SESD Landing Pad Layout				
3 Pin 2-ch 0402 Size Array				
Symbol	Millimeters	Inches		
Symbol	(mm)	(in)		
Α	0.60	0.024		
В	1.00	0.039		
С	0.225	0.009		
D	0.35	0.014		
D1	0.35	0.014		
E	0.15	0.006		
F	0.30	0.012		

PACKAGING

Packaging	Tape & Reel	Standard Box	
SESD0402Q2UG-0030-088	10,000	50,000	

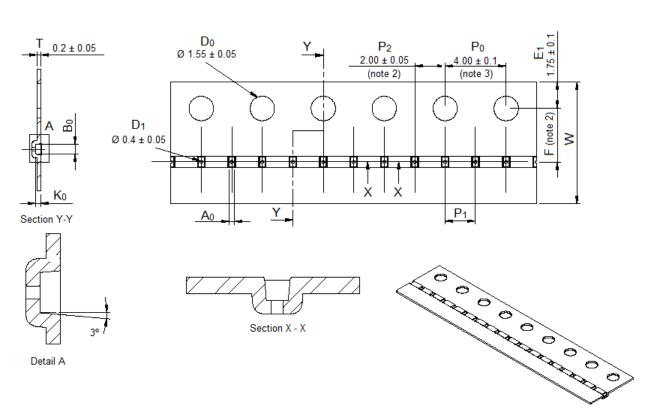




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CARRIER TAPE DIMENSIONS



A ₀	0.70 ± 0.05
Bo	1.15 ± 0.05
K ₀	0.47 ± 0.05
F	3.50 ± 0.05
P1	2.00 ± 0.10
W	8.00 ± 0.10

Note 1. All dimensions in mm

- Note 2. Measured from centerline of pocket to centerline of sprocket hole
- Note 3. Cumulative tolerance of 20 sprocket holes is ± 0.20

Note 4. Tolerances unless noted ± 0.20



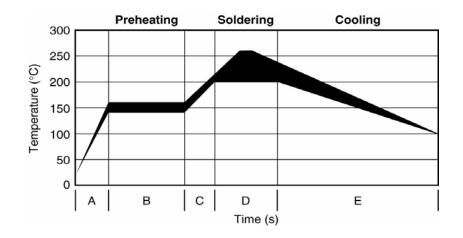
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SOLDER REFLOW RECOMMENDATION

А	Temperature ramp up 1	From ambient to Preheating temperature	30s to 60s
В	Preheating	140°C - 160°C	60s to 120s
С	Temperature ramp up 2	From Preheating to Main heating temperature	20s to 40s
D	Main heating	at 200°C at 220°C at 240°C at 260°C	60s ~ 70s 50s ~ 60s 30s ~ 40s 5s ~ 10s
Е	Cooling	From main heating temperature to 100°C	4°C/s (max)

FIGURE 4. REFLOW PROFILE



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